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AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A method of producing a crystal growth substrate, comprising:
molding a seed substrate into a desired shape so that irregularities are provided to a sapphire growth surface of said seed substrate;
growing a sapphire crystal on said sapphire growth surface of said seed substrate to thereby form a sapphire substrate; and
removing said seed substrate selectively from said sapphire substrate formed by said growing a sapphire crystal,
wherein said irregularities comprise cavities ~~are~~ formed periodically in said sapphire growth surface of said seed substrate during said molding a said seed substrate.
2. (Previously Presented) A method of producing a crystal growth substrate according to claim 1, wherein at least one of silicon (Si) and gallium arsenide (GaAs) is used as a material of said seed substrate.
3. (Previously Presented) A method of producing a crystal growth substrate according to claim 1, wherein chemical etching is performed in the removing of the seed substrate.
4. (Previously Presented) A method of producing a crystal growth substrate according to claim 1, further comprising:
heating said sapphire substrate formed by said growing a sapphire substrate at a high temperature of not lower than about 1000°C to thereby perform phase transition of said sapphire substrate from γ phase to α phase.
5. (Currently Amended) A method of producing a crystal growth substrate according to claim 1, wherein ~~the a shape of said irregularities provided to said sapphire growth surface of said seed substrate is formed by use of~~ cavities comprises each having part of a substantially spherical shape during said molding a seed substrate.

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6. (Previously Presented) A method of producing a crystal growth substrate according to claim 1, wherein said cavities are arranged two-dimensionally in said sapphire growth surface of said seed substrate.

7. (Previously Presented) A method of producing a semiconductor light-emitting element, said semiconductor light-emitting element capable of emitting planar light and including a semiconductor laminated on a sapphire substrate by crystal growth, said method comprising:
molding a seed substrate into a desired shape so that irregularities are provided to a sapphire growth surface of said seed substrate;
growing a sapphire crystal on said sapphire growth surface of said seed substrate to thereby form a sapphire substrate;
growing a desired semiconductor layer as a crystal on said sapphire substrate; and
removing said seed substrate selectively from said sapphire substrate formed by the growing of the sapphire substrate.

8. (Previously Presented) A method of producing a semiconductor light-emitting element according to claim 7, further comprising:
forming an electrode, the step being provided between the growing of the semiconductor crystal and the removing of the seed substrate.

9. (Previously Presented) A method of producing a semiconductor light-emitting element according to claim 7, wherein said semiconductor layer comprises a Group III nitride compound semiconductor containing " $\text{Al}_x\text{Ga}_y\text{In}_{1-x-y}\text{N}$ ($0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq x+y \leq 1$)" as a main component, which may contain impurities as an additive or may be free from impurities.

10 - 11. (Canceled)

12. (Original) A method of producing a crystal growth substrate according to claim 1, wherein said seed substrate is capable of being etched more easily than sapphire (Al_2O_3).

13. (Original) A method of producing a semiconductor light-emitting element according to claim 7, wherein said seed substrate is capable of being etched more easily than sapphire

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(Al₂O₃).

14. (Previously Presented) A method of producing a crystal growth substrate according to claim 1, wherein said growing a sapphire crystal comprises epitaxially growing a sapphire crystal by an ionized cluster beam vapor deposition and epitaxy method.

15. (Previously Presented) A method of producing a crystal growth substrate according to claim 1, wherein said sapphire crystal is grown at a growth temperature of substantially 350°C.

16. (Currently Amended) A method of producing a crystal growth substrate according to claim 1, wherein said ~~irregularities~~ cavities comprises cavities comprise substantially hemispherical convex portions.

17. (Currently Amended) A method of producing a crystal growth substrate according to claim ~~24~~ 1, wherein said ~~irregularities~~ protrusions comprise convex microlenses.

18. (Currently Amended) A method of producing a crystal growth substrate according to claim 1, wherein said ~~irregularities~~ cavities are uniformly spaced along said sapphire growth surface.

19. (Currently Amended) A method of producing a crystal growth substrate according to claim 1, wherein said ~~irregularities~~ cavities are provided in an array across said sapphire growth surface.

20. (Currently Amended) A method of producing a semiconductor light-emitting element, comprising:

growing a desired semiconductor layer as a crystal on a sapphire substrate grown on a seed substrate; and

removing said seed substrate,

wherein cavities are formed periodically in a sapphire growth surface ~~substrate~~ of said seed substrate.

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21. (New) A method of producing a semiconductor light emitting element according to claim 7, wherein said irregularities comprise cavities formed periodically in said sapphire growth surface of said seed substrate during said molding a seed substrate.
22. (New) A method of producing a semiconductor light emitting element according to claim 21, wherein said cavities form protrusions on a surface of said sapphire substrate.
23. (New) A method of producing a semiconductor light emitting element according to claim 22, wherein said protrusions comprise convex microlenses.
24. (New) A method of producing a crystal growth substrate according to claim 1, wherein said cavities form protrusions on a surface of said sapphire substrate.
25. (New) A method of producing a semiconductor light emitting element according to claim 7, where a surface of said sapphire substrate that is formed on said sapphire growth surface comprises a light-emitting surface
26. (New) A method of producing a semiconductor light emitting element according to claim 7, wherein said removing said seed substrate is performed after said growing said semiconductor layer.
27. (New) A method of producing a crystal growth substrate according to claim 1, wherein said cavities comprise a curved portion.